

0995791.062901  
T06290" T6256250

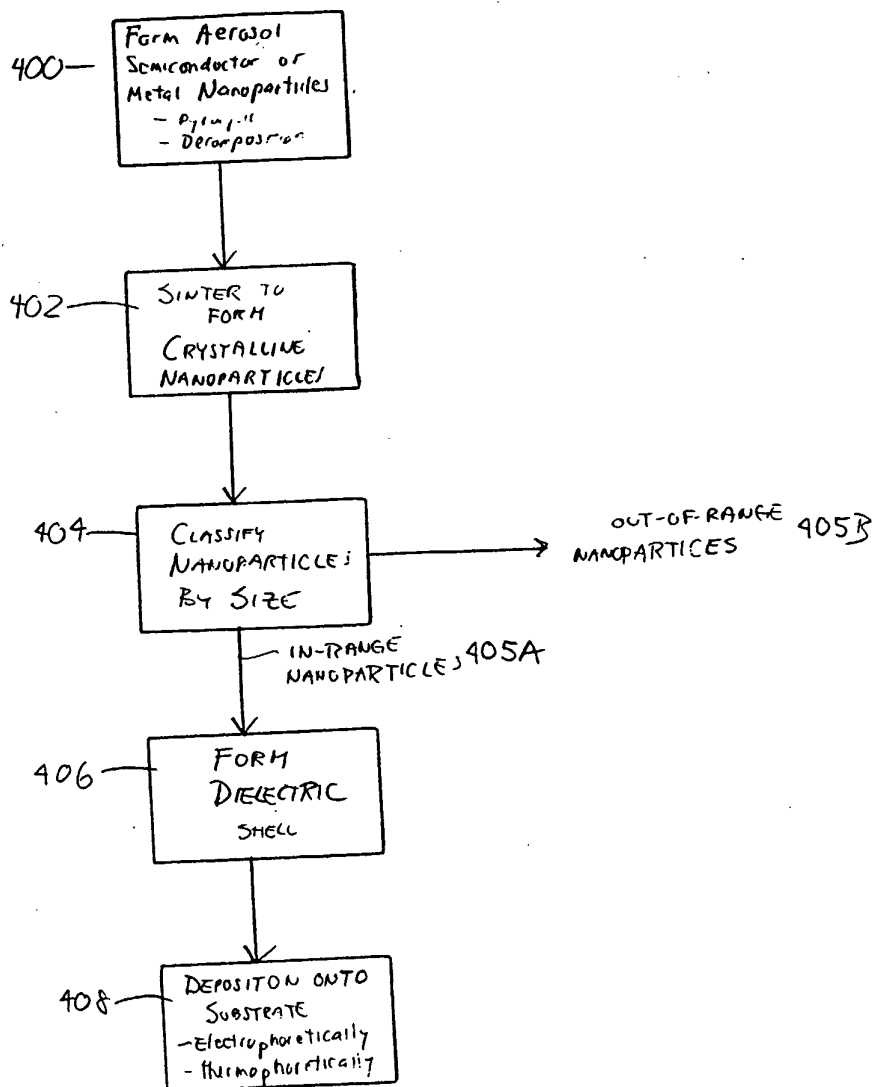


FIGURE 1

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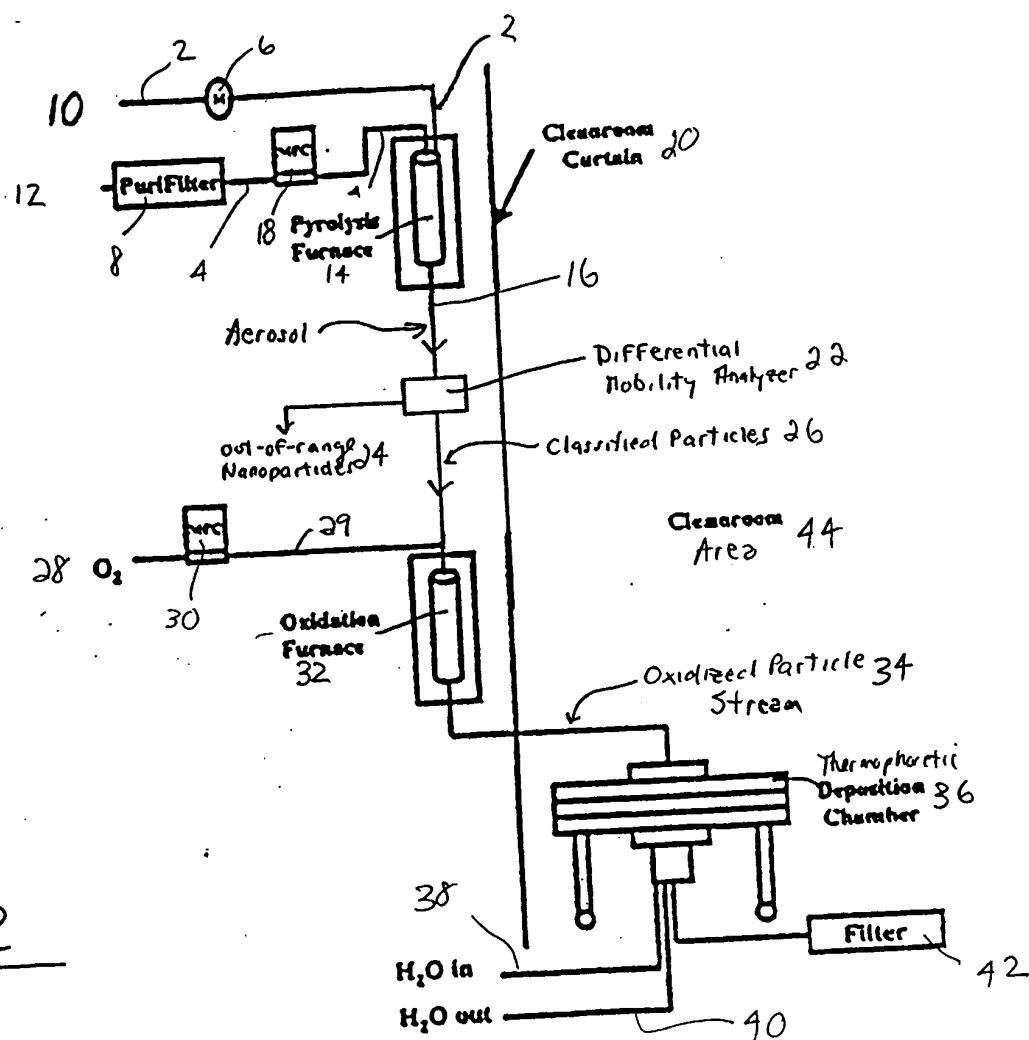


FIGURE 2

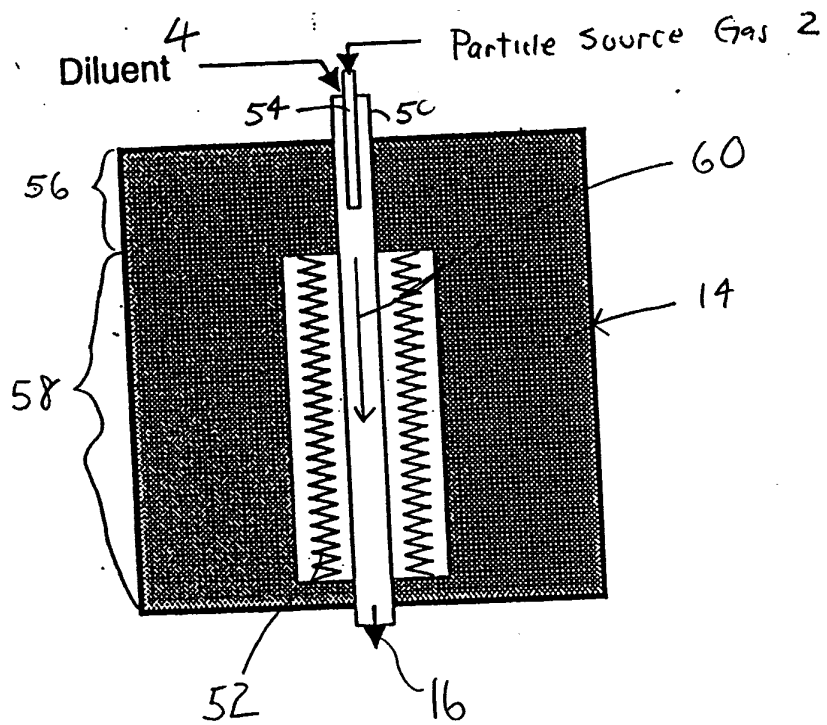


FIGURE 3

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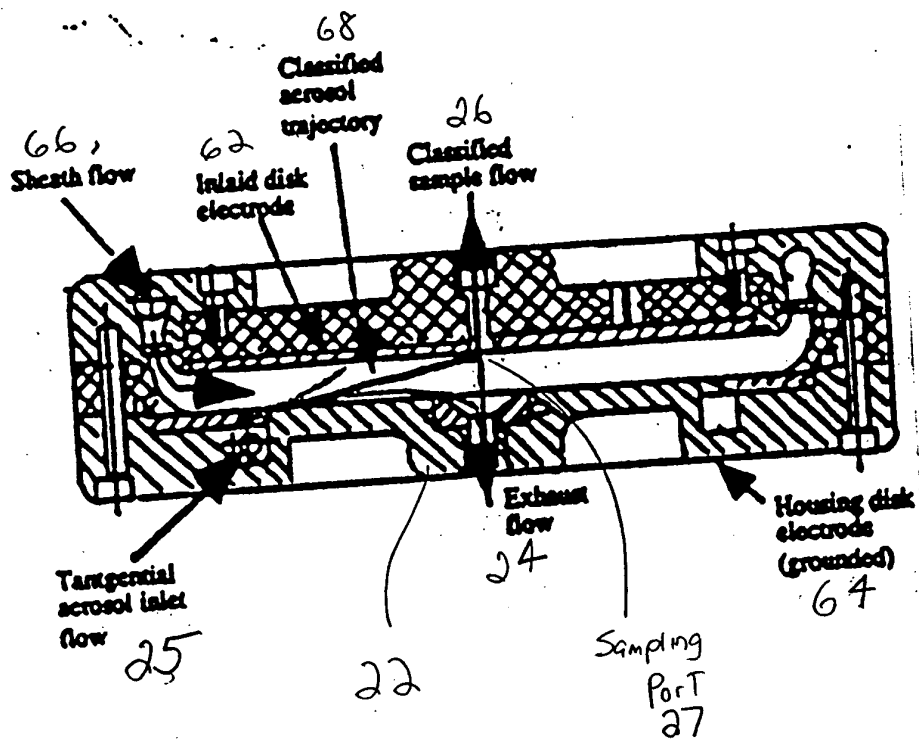


FIGURE 4

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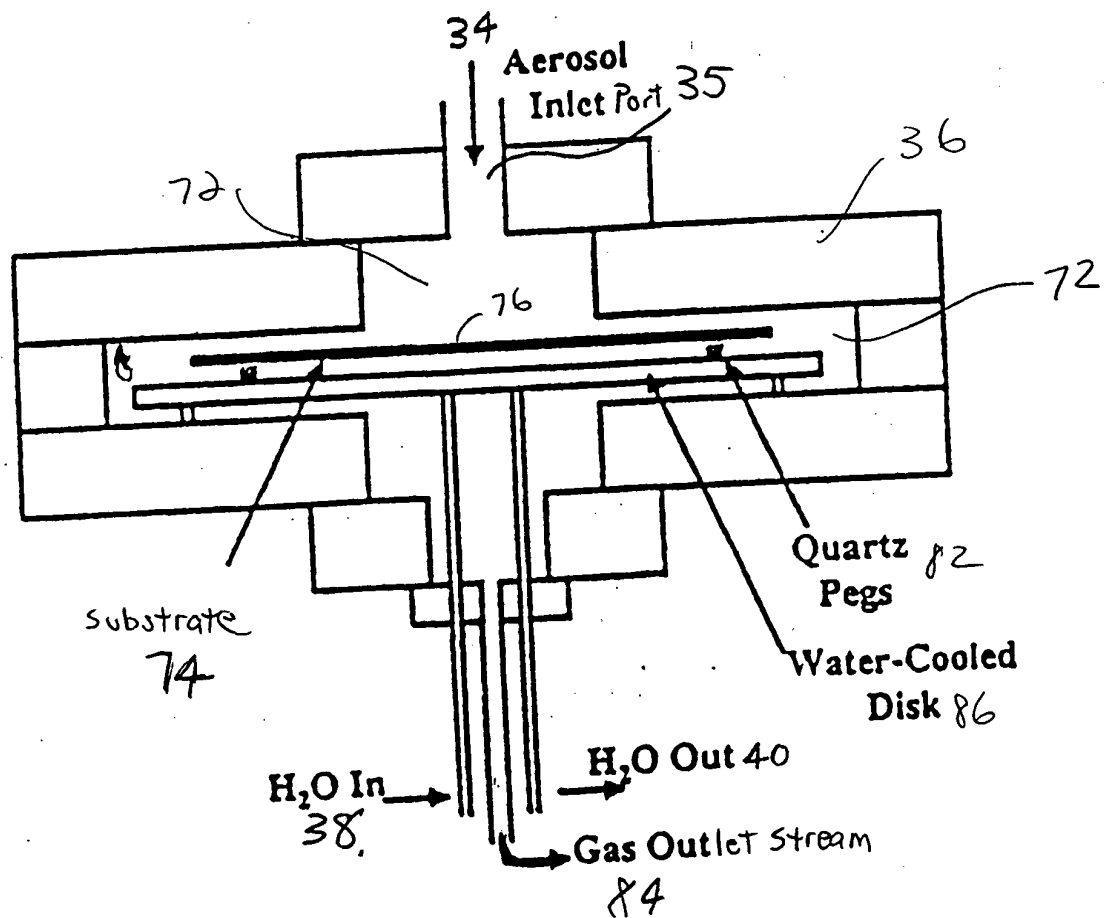


FIGURE 5

FIGURE 6

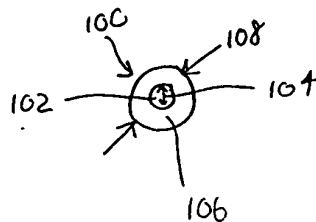


FIGURE 7

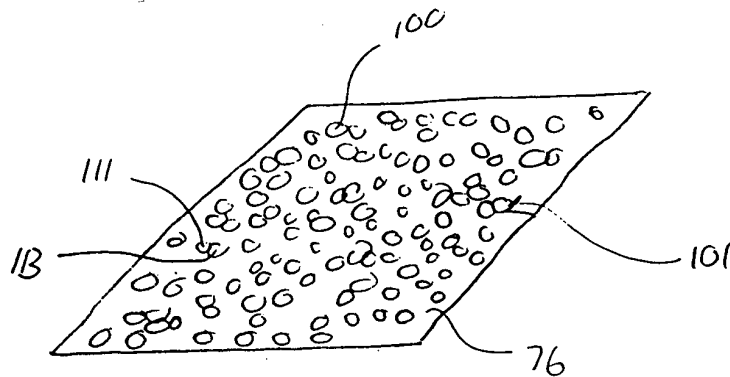


FIGURE 8

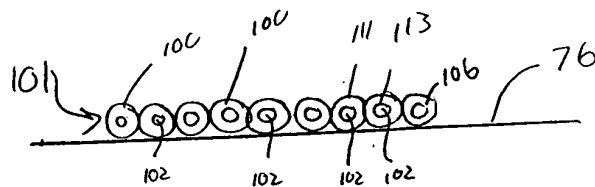
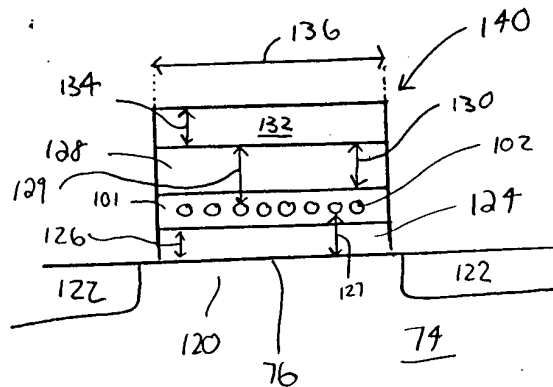


FIGURE 10



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FIGURE 9

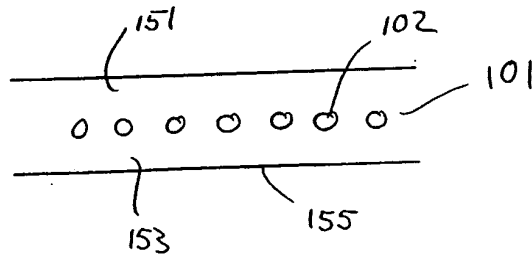
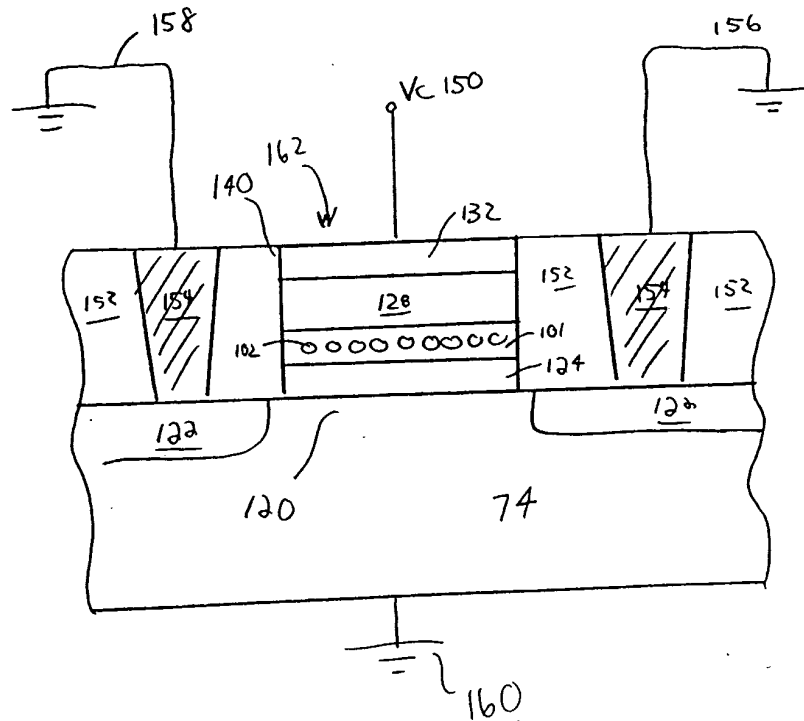


FIGURE 11



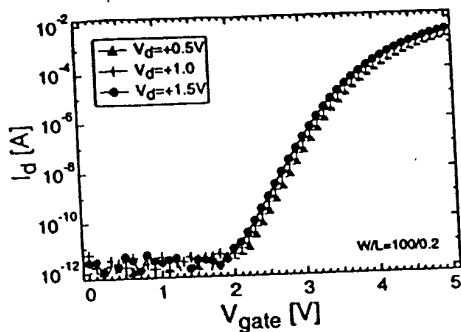


FIG 12 .. Subthreshold characteristics of a  $0.2\mu\text{m}$  n-type aerosol-nanocrystal floating-gate MOSFET (subthreshold slope =  $200\text{mV/dec}$ ; DIBL =  $100\text{mV/V}$ ).

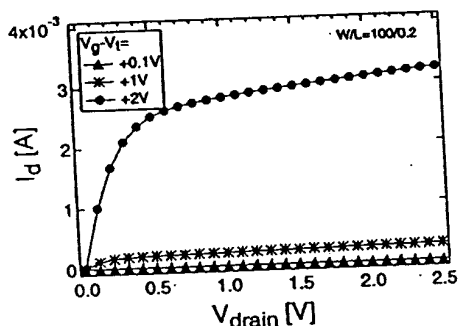


FIG 13 Output characteristics of a  $0.2\mu\text{m}$  aerosol-nanocrystal floating-gate MOSFET; drive current =  $30\mu\text{A}/\mu\text{m}$ .

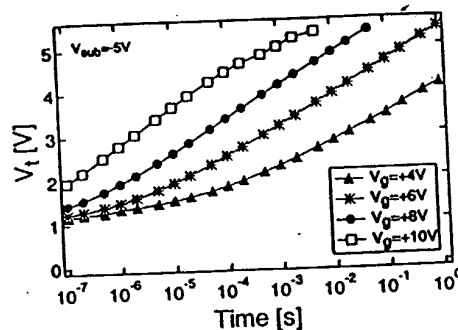


FIG 14: Programming transients (uniform FN tunneling) of the nanocrystal NVM device.

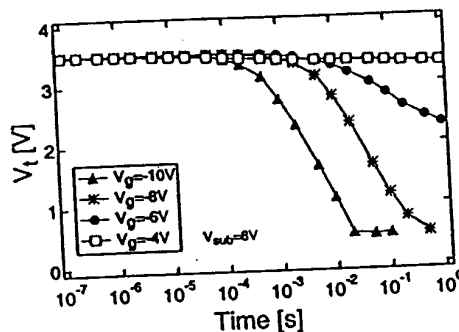


FIG 15 Erase transients (uniform FN tunneling).

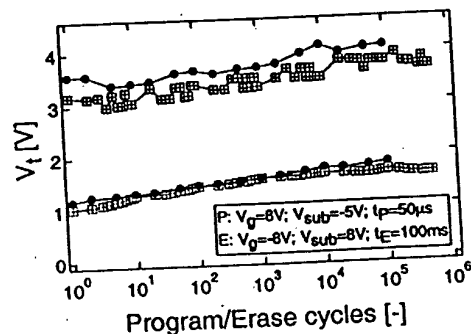


FIG 16: Endurance characteristic; only limited window closure is observed after  $10^5$  program/erase cycles.

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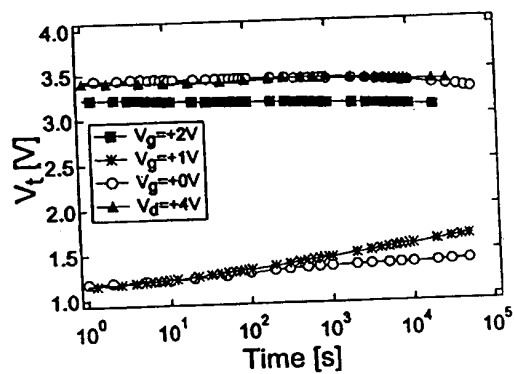


FIGURE 17